BMF65N380C1

Super Junction Power MOSFET

650 V, 10.5 A, 380 mΩ

Description

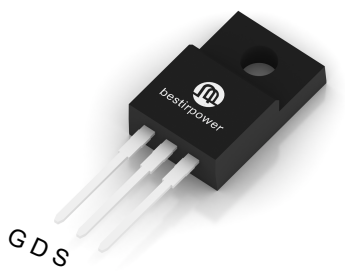
BMx65N380C1 is power MOSFET using bestirpower's advanced super junction technology that can realize very low on-resistance and gate charge.
It will provide much high efficiency by using optimized charge coupling technology. These user friendly devices give an advantage of Low EMI to designers as well as low switching loss.

Features

$BV_{DSS,\ Tc=25℃}$	$I_{D,\ Tc=25℃}$	$R_{DS(on),max.\ Tc=25℃}$	$Q_{g,typ}$
650 V	10.5 A	380 mΩ	23.5 nC

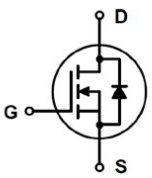
- Ultra-fast body diode.
- Extremely low losses due to very low FOM Rdson*Qg and Eoss.
- Very high commutation ruggedness.

TO-220F



Applications

- PFC.
- Adapter.
- LCD TV.
- LED lighting.
- UPS.



Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method
BMP65N380C1	BMP65N380C1	TO220	Tube
BMF65N380C1	BMF65N380C1	TO220F	Tube
BMB65N380C1	BMB65N380C1	TO263	Tape & Reel
BMD65N380C1	BMD65N380C1	TO252	Tape & Reel

Absolute Maximum Ratings (T_J = 25℃ unless otherwisenoted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		650	V
V_{GSS}	Gate to Source Voltage		±30	V
I_D	Drain Current[1]	V_{GS} = 10 V, (T_C= 25℃)	10.5	A
		V_{GS} = 10 V, (T_C= 100℃)	6.6	
I_{DM}	Drain Current	Pulsed	31	A
P_D	Power Dissipation For TO-220F		32	W
	Power Dissipation For TO-220, TO-252, TO-263		104.2	
E_{AS}	Single Pulsed Avalanche Energy[2]		225	mJ
dv/dt	Diode Recovery dv/dt[3]		15	V/ns
I_S	Continuous diode forward current T_C=25°C		10.5	A
$I_{S,pulse}$	Diode pulse current[1]		31	A
T_{STG}	Storage Temperature Range		-55 to 150	℃
T_J	Maximum Operating Junction Temperature		150	℃
T_L	Maximum Lead Temperature for Soldering, 1/8” from Case for 10		260	℃

1) Pulse width t_p limited by T_j,max.
2) V_{DD}=50V, R_G=25Ω, Starting T_j=25°C.
3) V_{DClink}=400V; $V_{DS,peak}$<$V_{(BR)DSS}$; identical low side and high side switch with identical R_G.

Thermal Characteristics (FullPAK) TO220F

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.9	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

Thermal Characteristics (Non FullPAK) TO220, TO252, TO263

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.2	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62	

Electrical Characteristics (T_J = 25℃ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250μA	650	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 650 V, V_{GS} = 0 V T_J=25°C	-	-	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	2.0	3.0	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 5.5A,T_J=25°C	-	340	380	mΩ
R_G	Gate Resistance	f = 1.0MHz ,open drain	-	4	-	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=50V, f=1MHz	-	630	-	pF
C_{oss}	Output Capacitance		-	33	-	pF
C_{rss}	Reverse Transfer Capacitance		-	1.4	-	pF
$C_{o(er)}$	Effective output capacitance, energy related[1)]	V_{GS}=0V, V_{DS}= 0 to 400V	-	25	-	pF
$C_{o(tr)}$	Effective output capacitance, time related[2)]		-	128	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V, V_{DD} =480V, I_D =5A	-	23.5	-	nC
Q_{gs}	Gate to Source Charge		-	2.5	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	9	-	nC
Vplateau	Gate plateau voltage		-	5	-	V
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 480V, I_D = 5A, V_{GS} =0 to 10V	-	57	-	ns
t_r	Turn-On Rise Time		-	30	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	73	-	ns
t_f	Turn-Off Fall Time		-	15	-	ns
Reverse Diode Characteristics						
V_{SD}	Diode Forward Voltage	I_F=5.5A, V_{GS} = 0V T_J=25°C	-	0.85	-	V
t_{rr}	Reverse Recovery Time	V_R = 480V, I_F =5A di_F/dt = 100A/μs	-	210	-	ns
Q_{rr}	Reverse Recovery Charge		-	1.29	-	μC
I_{rrm}	Peak Reverse Recovery Current		-	16	-	A

1) $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V.
2) $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V.

Typical Performance Characteristics

Figure 1: Transient Thermal Impedance For TO-220F

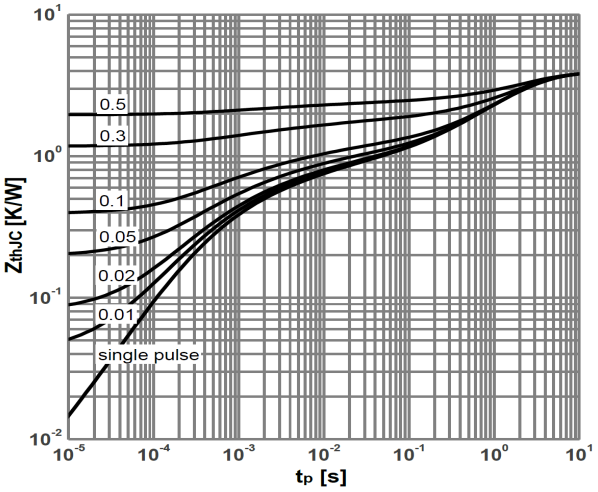


Figure 2: Power dissipation For TO-220F

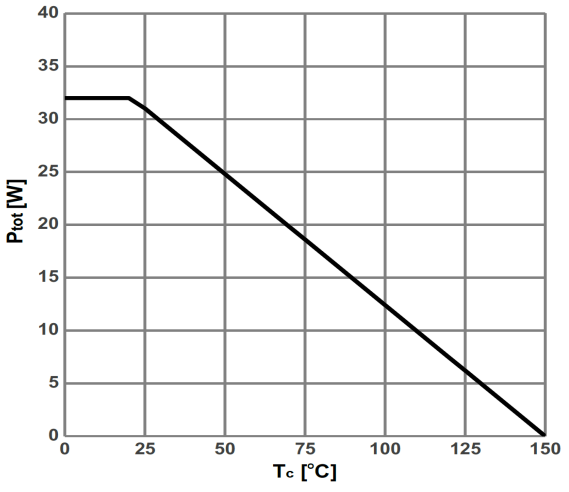


Figure 3. Transient Thermal Impedance For TO-220、TO-252、TO-263

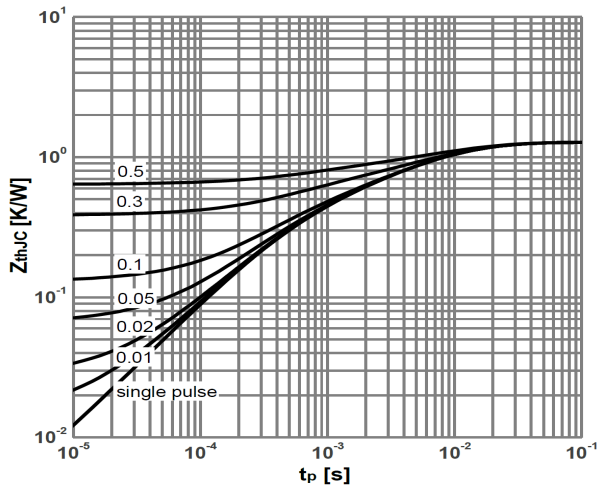


Figure 4. Power dissipation For TO-220、TO-252、TO-263

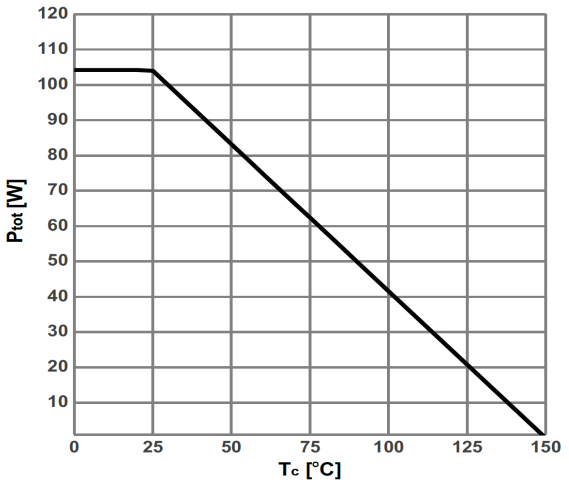


Figure 5: Safe operating area For TO-220、TO-252、TO-263

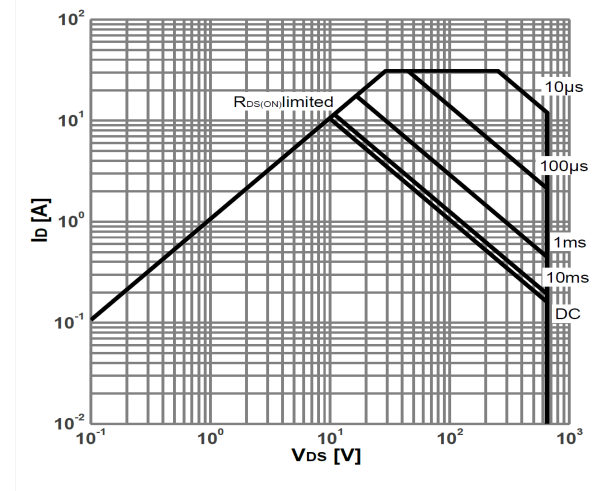
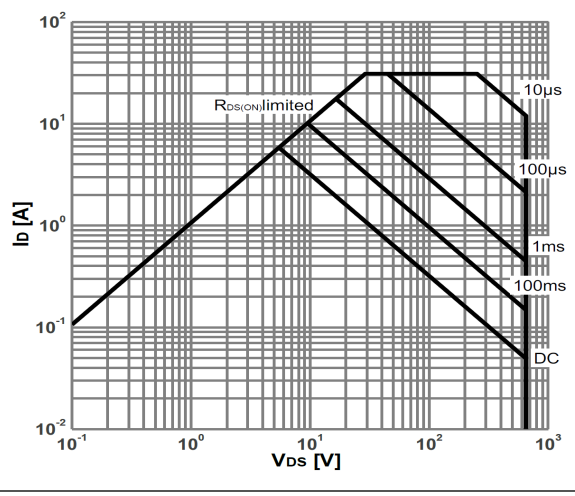


Figure 6: Safe operating area For TO-220F



Typical Performance Characteristics

Figure 7: Typ. output characteristics @ Tj=25°C

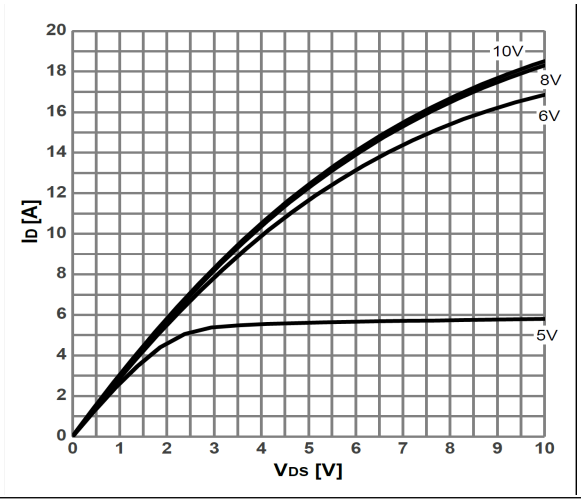


Figure 8: Typ. output characteristics @ Tj=125°C

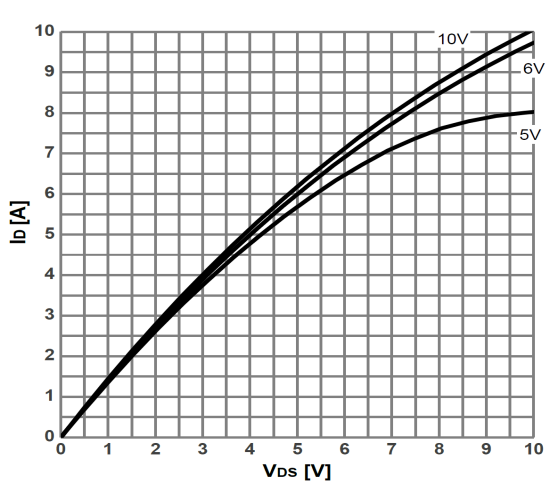


Figure 9: Typ. drain-source on-state resistance

$R_{DS}(on)=f(I_D)$; $T_j=25°C$; parameter: V_{GS}

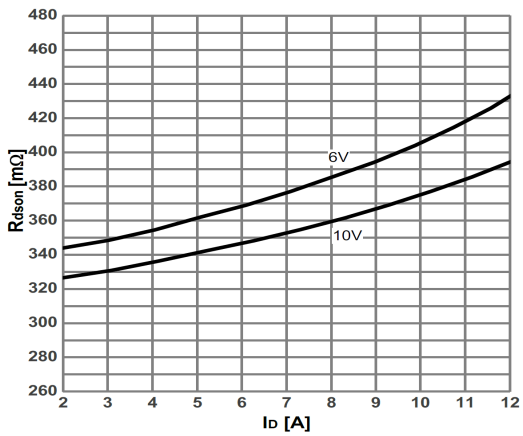


Figure 10: Drain-source on-state resistance

$R_{DS}(on)=f(T_j)$; $I_D=5.5A$; $V_{GS}=10V$

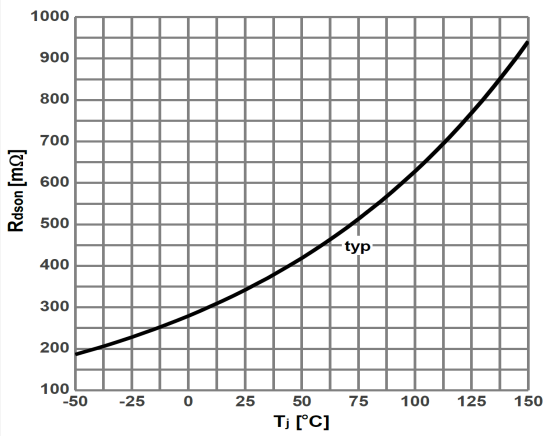


Figure 11: Typ. transfer characteristics

$I_D=f(V_{GS})$; $V_{DS}=20V$; parameter: T_j

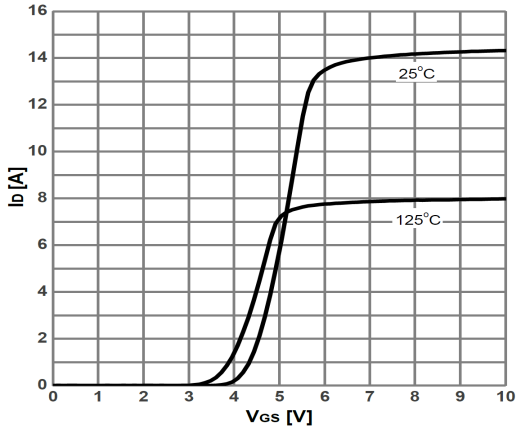
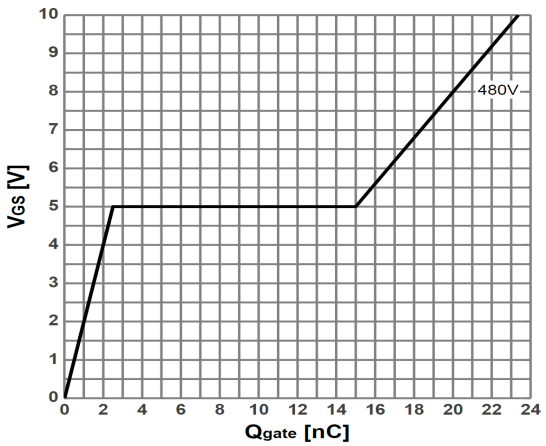


Figure 12: Typ. gate charge

$V_{GS}=f(Q_{gate})$; $I_D=5A$ pulsed; $V_{DS}=480V$



Typical Performance Characteristics

Figure 13: Forward characteristics of reverse diode

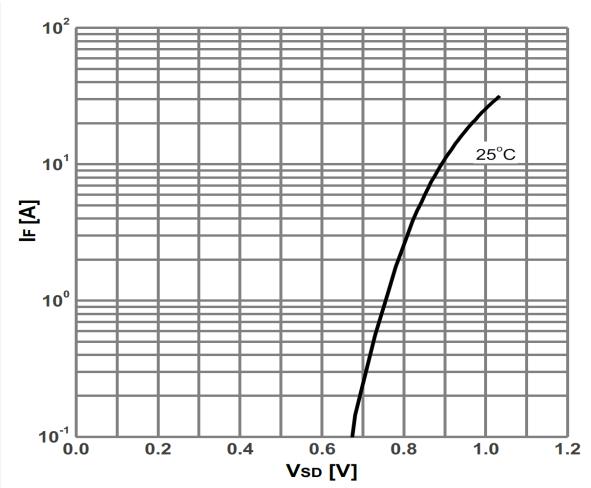


Figure 14: Drain-source breakdown voltage

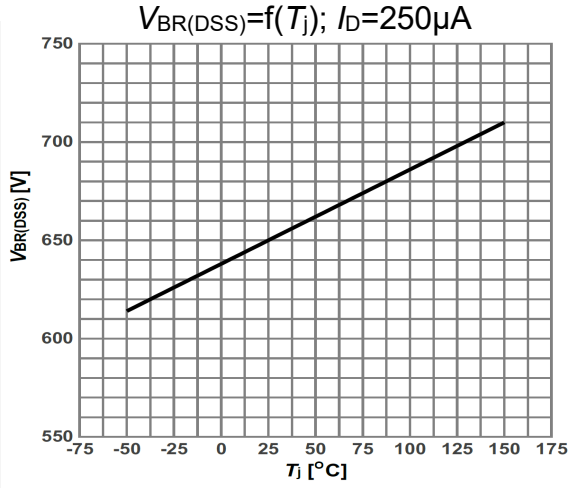


Figure 15: Typ. capacitances

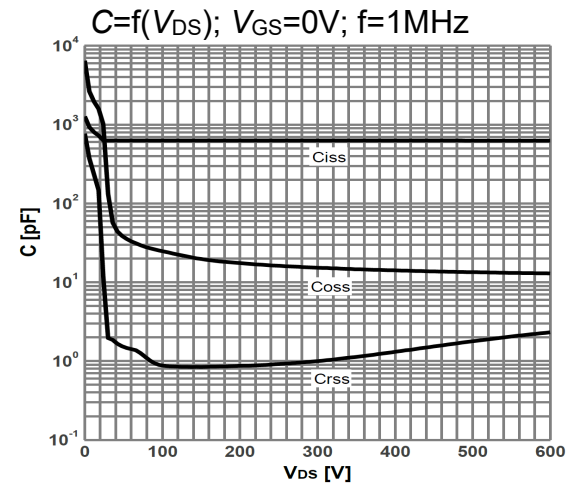
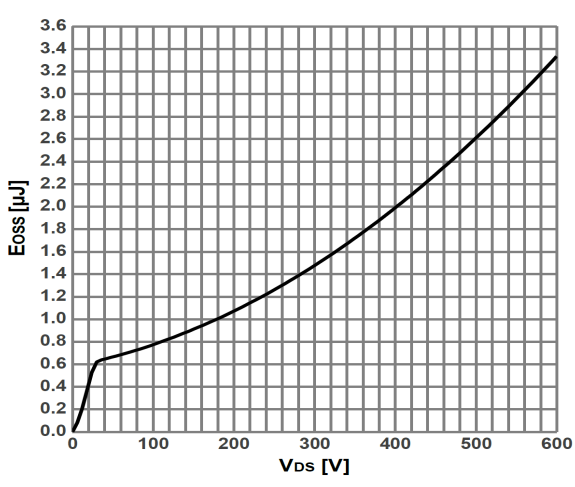


Figure 16: Typ. Coss stored energy



Test Circuits

Figure 17. Diode Characteristics

Test circuit for diode characteristics and Diode recovery waveform

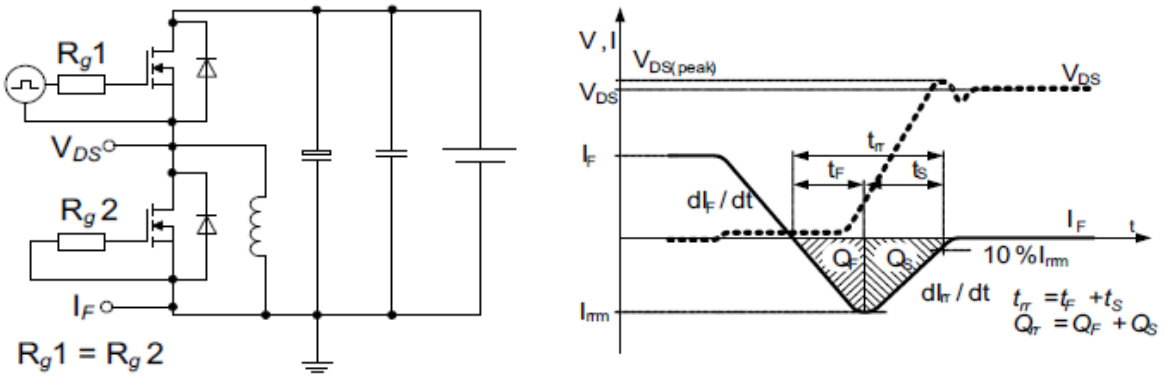


Figure 18. Switching Times

Switching times test circuit for inductive load and Switching times waveform

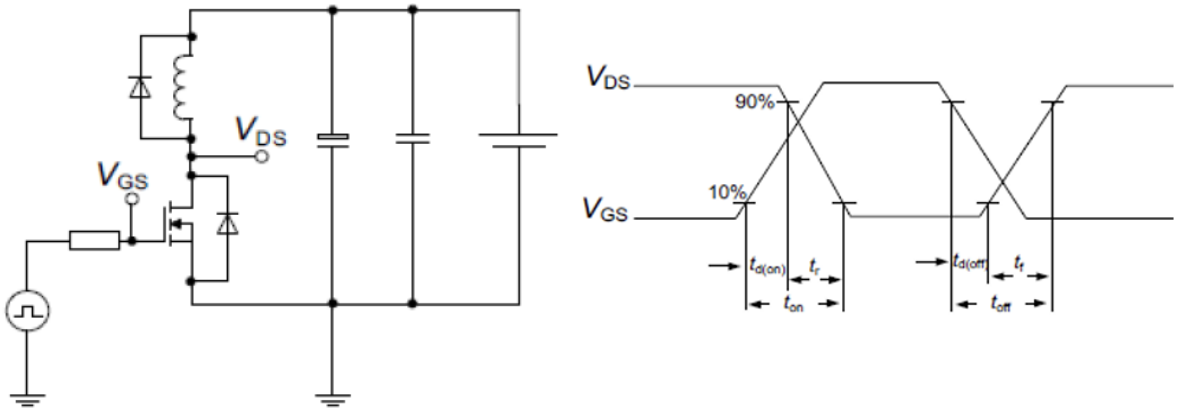
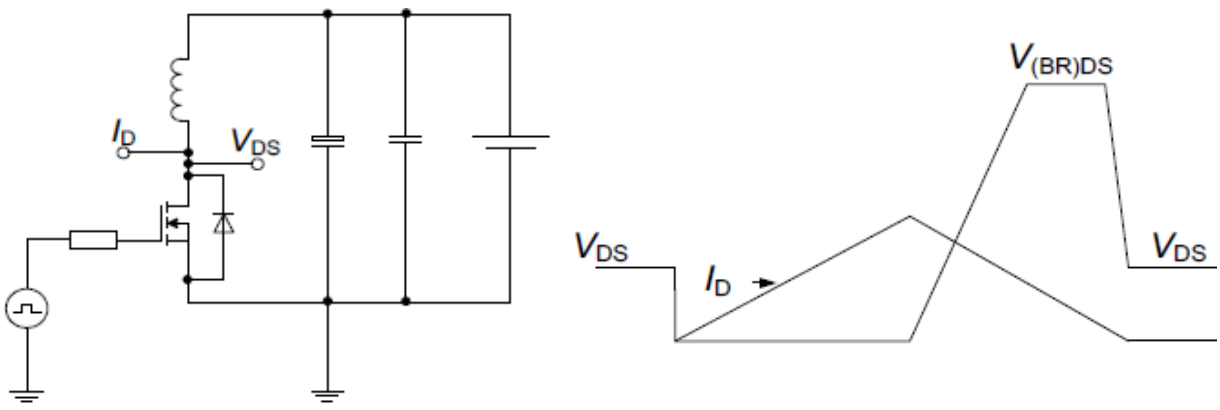


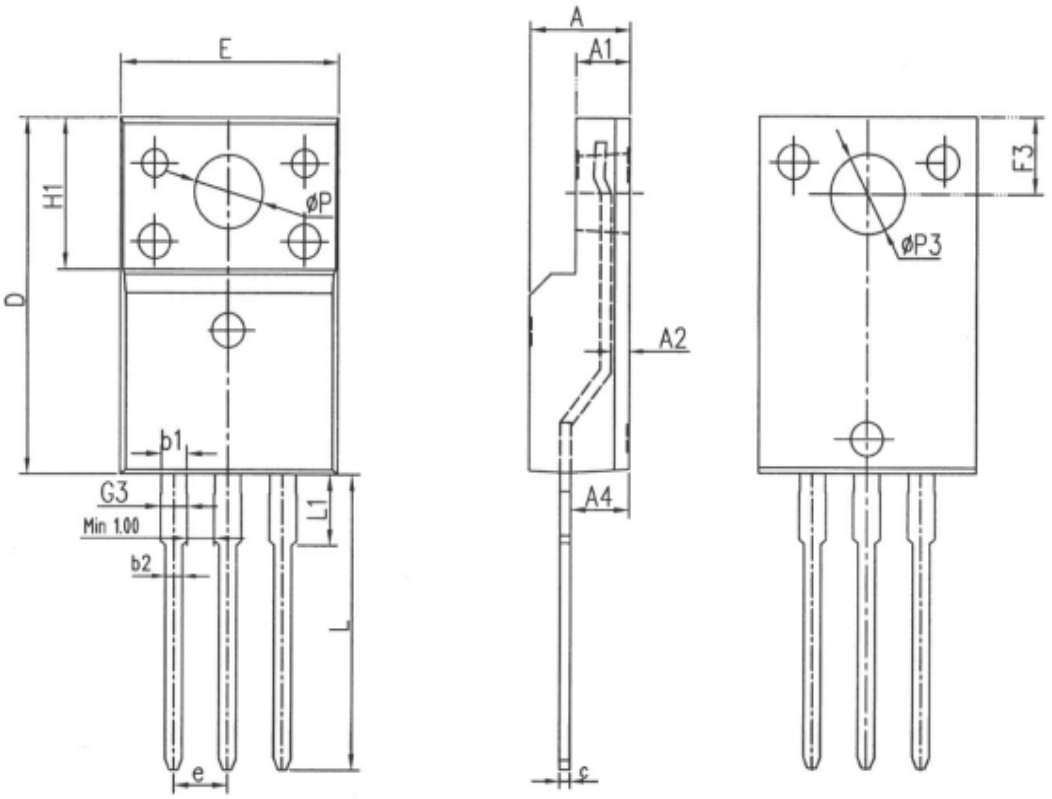
Figure 29. Unclamped Inductive Load

Unclamped inductive load test circuit and Unclamped inductive waveform



Package Outlines

TO-220F



COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
E	10.00	10.20	10.40
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.65	0.85	1.30
A4	2.55	2.75	2.95
c	0.40	0.50	0.65
D	15.57	15.87	16.17
H1	6.70REF		
e	2.54BSC		
ΦP	3.183REF		
L	12.68	12.98	13.28
L1	3.25	3.45	3.65
ΦP3	3.45REF		
F3	3.10	3.30	3.50
G3	1.10	1.30	1.50
b1	1.05	1.20	1.35
b2	0.70	0.80	0.92

* Dimensions in millimeters

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